
2SB1103

Silicon PNP Triple Diffused

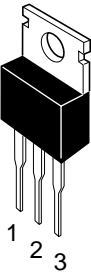
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Application

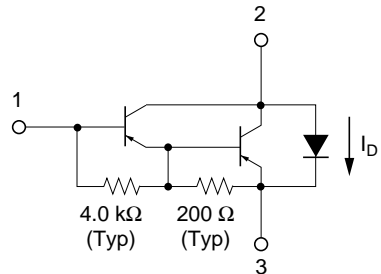
Low frequency power amplifier

Outline

TO-220AB



- 1. Base
- 2. Collector (Flange)
- 3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-8	A
Collector peak current	$I_{C(\text{peak})}$	-12	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
C to E diode forward current	I_D^{*1}	8	A

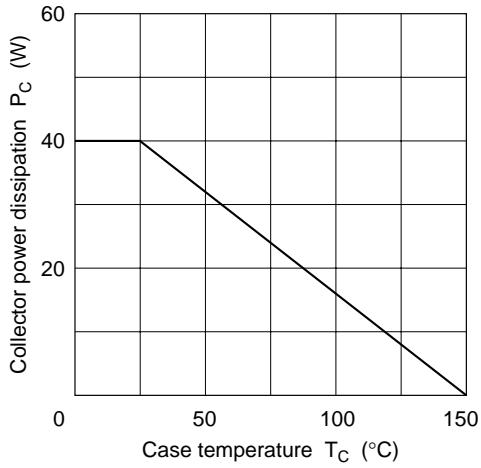
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

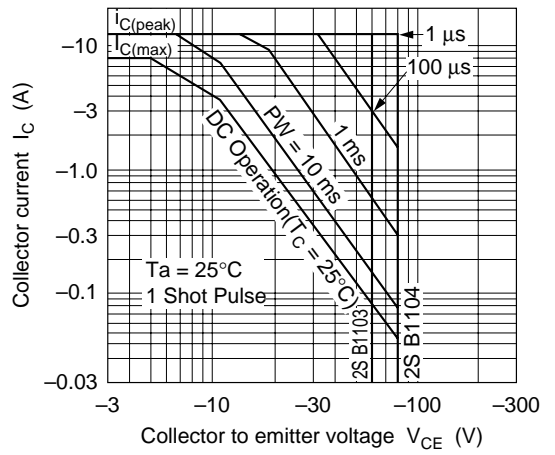
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -25 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -60 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -50 \text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3 \text{ V}$, $I_C = -4 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})1}$	—	—	-1.5	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{CE(\text{sat})2}$	—	—	-3.0		$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(\text{sat})1}$	—	—	-2.0	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{BE(\text{sat})2}$	—	—	-3.5		$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 8 \text{ A}^{*1}$
Turn on time	t_{on}	—	0.5	—	μs	$I_C = -4 \text{ A}$,
Storage time	t_{stg}	—	3.0	—		$I_{B1} = -I_{B2} = -8 \text{ mA}$
Fall time	t_f	—	1.0	—		

Note: 1. Pulse Test.

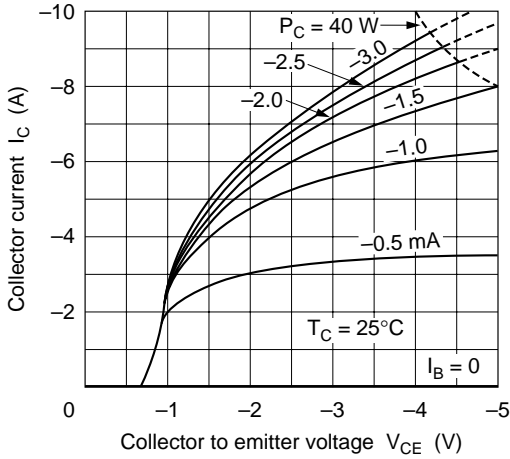
Maximum Collector Dissipation Curve



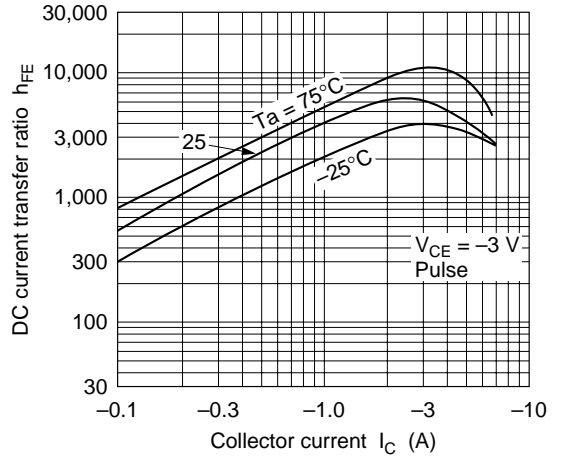
Area of Safe Operation



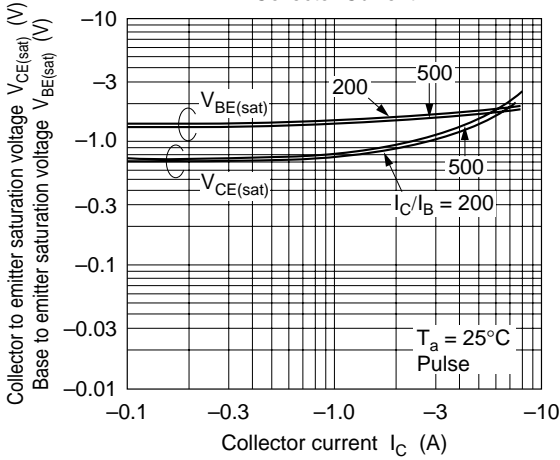
Typical Output Characteristics



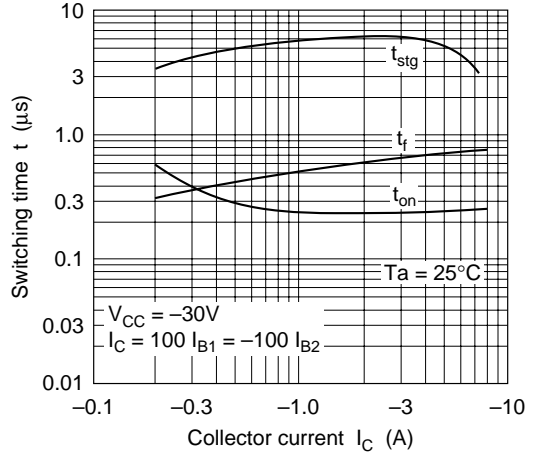
DC Current Transfer Ratio vs. Collector Current

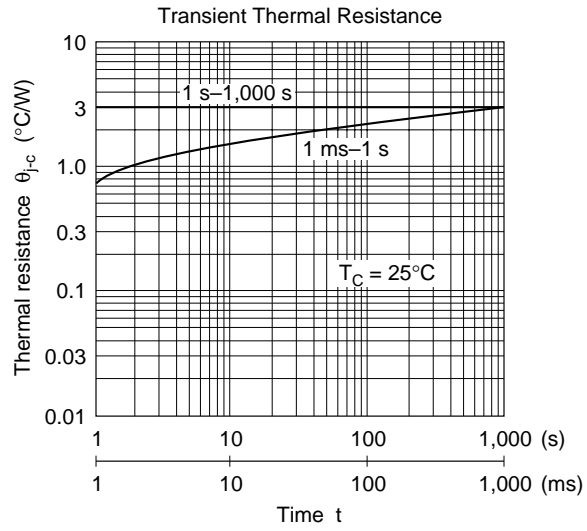


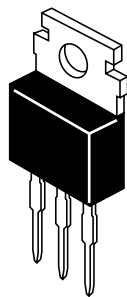
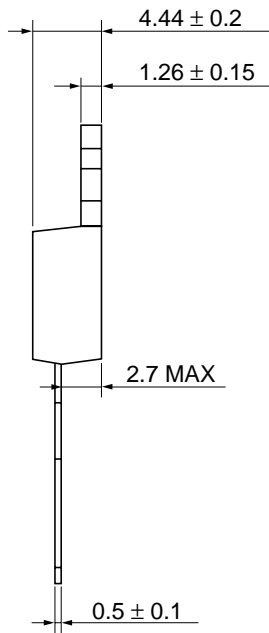
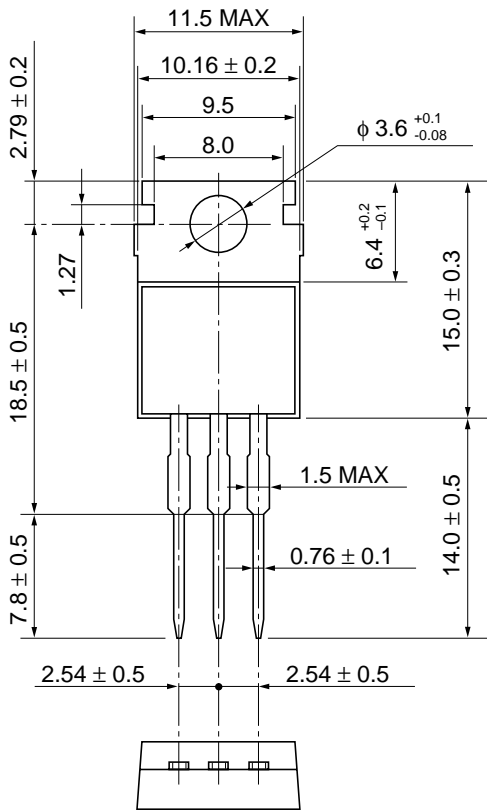
Saturation Voltage vs. Collector Current



Switching Time vs. Collector Current







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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